Samsung GBBM DWSwap User Manual

General Description and Name

Samsung GBBM or GBBM DWSwap. This method is a relatively standard bad blocking scheme that allocates a reserved block area (RBA) at the end of the device. There is a map table containing a list of bad blocks and the replacement block for each bad block.

Relevant User Options

The following special features on the special features tab apply to this scheme. The default values might work in some cases but please make sure to set the right value according to your system.
Please note only the below special feature items are related to this scheme and ignore any others. If any of below items doesn't exist, please check whether the right version has been installed or contact Data I/O for support by submitting Device Support Request through this address:
http://www.dataio.com/support/dsr.asp

Bad Block Handling Type =   "Samsung GBBM DWSwap"

Spare area :   Please refer to "Description of common NAND special features.pdf". *Always set as " ECC " for this BBM*.[Default 'Disabled']

RBA area: Number of blocks = "35"

RBA area: Start block = "2013"

Required good block area: Start block = "0" Please refer to "Description of common NAND special features.pdf".

Required good block area: Number of blocks = "0" Please refer to "Description of common NAND special features.pdf".

Special Notes

The spare area in this scheme uses a special ECC method provided by Samsung. However, the bad block marks are always located in the spare area (Byte 517 for x8 devices).

The data file doesn't have to be arranged in any special way for this scheme. The binary that should be placed into the device is all that is needed.

Revision History

V1.0   June 11, 2009
        Create this spec.

Appendix

You can get the file "Description of common NAND special features.pdf" from
http://ftp.dataio.com/FCNotes/BBM/